

# UV SiC Avalanche Photodiode

## UV SiC APD

UV Solar Blind Silicon Carbide (SiC) Avalanche Photodiode for low-signal applications in UV-range

### Specifications

Sensitivity:	1 nW/cm <sup>2</sup>
Signal enhancement:	10 <sup>5</sup> ... 10 <sup>6</sup>
BIAS Volt:	180 VDC
APD detection size:	1.2 mm
APD size:	4 mm × 4 mm

The silicon carbide (SiC) UV APD has many of the characteristics of other APDs in that it is extremely sensitive and has high signal amplification, but is only sensitive to UV radiation (see figures).

Since the substrate is made of more resistant SiC, the bias voltage is higher than silicon-based devices, about 180 VDC

